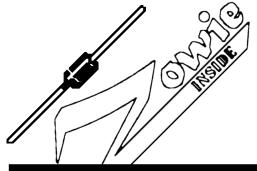


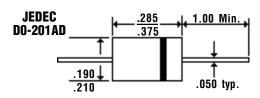
EGPZ30A . . . 30M Series

Preliminary Data Sheet | 3.0 Amp Glass Passivated | Sintered Fast Efficient **№ Rectifiers**

Semiconductor Description

Mechanical Dimensions





Features

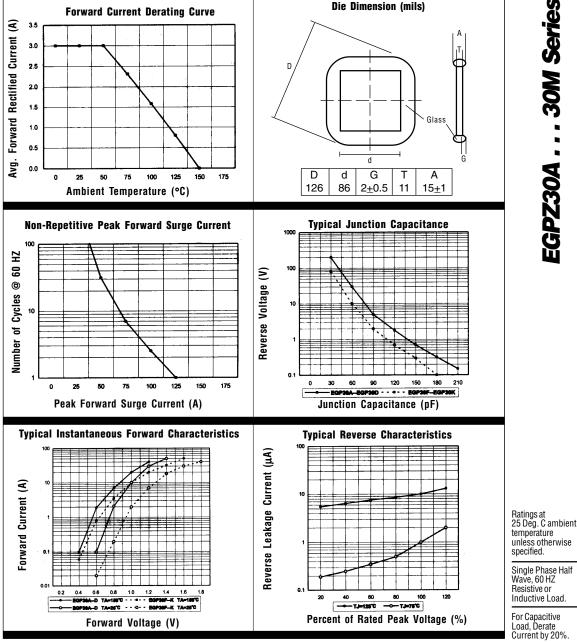
- LOWEST COST FOR GLASS SINTERED **FAST EFFICIENT CONSTRUCTION**
- LOWEST V, FOR GLASS SINTERED FAST EFFICIENT CONSTRUCTION
- TYPICAL I_R < 100 nAmps

- 3.0 AMP OPERATION @ $T_A = 55$ °C, WITH **NO THERMAL RUNAWAY**
- SINTERED GLASS CAVITY-FREE **JUNCTION**

Electrical Characteristics @ 25°C.	EGPZ30A 30M Series							Units
Maximum Ratings	30A	30B	30D	30G	30J	30K	30M	
Peak Repetitive Reverse VoltageV _{RRM}	50	100	200	400	600	800	1000	Volts
RMS Reverse VoltageV _{R(rms)}	35	70	140	280	420	560	700	Volts
DC Blocking Voltage $V_{\rm DC}$	50	100	200	400	600	800	1000	Volts
Average Forward Rectified CurrentI _{F(av)} Current 3/8" Lead Length @ T _A = 55°C				3.0				Amp
Non-Repetitive Peak Forward Surge CurrentI _{FSM} 8.3mS, ½ Sine Wave Superimposed on Rated Load	125							Amp
Forward Voltage @ Rated Forward Current and 25°CV _F	<	1.0 .	>	1.3	<	1.7	>	Volts
DC Reverse CurrentI _{R(max)} @ Rated DC Blocking Voltage $T_A = 25^{\circ}C$ $T_A = 125^{\circ}C$								μΑmp μΑmp
Typical Junction CapacitanceC _J (Note 1)				60 .				pF
Maximum Thermal ResistanceR _{eJA} (Note 2)				16 .				°C/W
Maximum Reverse Recovery Timet _{RR} (Note 3)	<		50		· <	75	>	nS
Operating & Storage Temperature Range T_{J} , T_{STRG}				-65 to 15	50			°C



Preliminary Data Sheet | 3.0 Amp Glass Passivated | Sintered Fast Efficient Rectifiers



NOTES: 1. Measured @ 1 MHZ and applied reverse voltage of 4.0V.

- 2. Thermal Resistance from Junction to Ambient at 3/8" Lead Length, P.C. Board Mounted.
- 3. Reverse Recovery Condition $I_F = 0.5A$, $I_R = 1.0A$, $I_{RR} = 0.25A$.